

### Comment on the "Evidence for a Self-Confined Plasma" in Laser Annealing

Aydinli, Lo, Lee, and Compaan<sup>1</sup> (ALLC) report the spectral dependence of the induced absorption of silicon on sapphire under intense laser illumination. They claim that these results are due to the existence of an electron-hole plasma with a density of  $4 \times 10^{22} \text{ cm}^{-3}$ , providing evidence for the self-confined plasma predicted by Van Vechten and Wautelet.<sup>2</sup> We think that this conclusion is erroneous for the following reasons:

(1) The optical properties of an  $e-h$  plasma with densities of the order of  $4 \times 10^{22} \text{ cm}^{-3}$  do not fit at all the experimental results. The study<sup>3</sup> of  $e-h$  droplets in Si gives the average energy, for  $T \ll T_F$  the Fermi temperature,  $\epsilon \approx 5.3 \times 10^{-12} n^{2/3} - 11.2 \times 10^{-6} n^{1/3}$  where  $\epsilon$  is in meV and  $n$  in  $\text{cm}^{-3}$  (the correlation energy being negligible at large  $n$ ). So for  $n = 4 \times 10^{22} \text{ cm}^{-3}$ ,  $\epsilon = 6.2 \text{ eV}$ ,  $E_F^e + E_F^h \approx 10 \text{ eV}!!$  (if one assumes the same effective mass) and  $T_F \sim 60\,000 \text{ K}$  which means that the plasma is cold even at the melting point. The resulting "optical gap" or threshold energy for band-to-band absorption should be at  $E_0 = 11.5 \text{ eV}$ , in contradiction with the observed absorption which shows little shift compared to the one of Si with no excess  $e-h$  pairs. For  $1.3 \text{ eV} < h\nu < 3.3 \text{ eV} \ll E_0$  the optical properties of such a dense plasma should be that of a metal.

(2) Our second point concerns the possibility of forming a  $4 \times 10^{22} \text{ cm}^{-3}$  plasma which is confined in  $0.07 \mu\text{m}$  and which lasts the 70 nsec during which the high reflectivity is seen. The key point for the self-confinement found by Van Vechten and Wautelet rests on the hypothesis that in a dense plasma the electron-phonon interaction has disappeared as well as the Auger recombination. One usually believes that the  $e-h$  lifetime decreases with density as  $(Cn^2)^{-1}$ , with  $C = 4 \times 10^{-31} \text{ cm}^6 \text{ s}^{-1}$  in Si, and saturates for  $n > 10^{21} \text{ cm}^{-3}$  at  $\tau_0 \sim 6 \times 10^{-12} \text{ s}$  because of screening. ALLC's pulse ( $W = 1 \text{ J cm}^{-2}$ ,  $\lambda = 485 \text{ nm}$ ,  $\tau = 8 \text{ nsec}$ ) creates  $F = 3.1 \times 10^{26} \text{ photons cm}^{-2} \text{ s}^{-1}$  (if one forgets the reflectivity). The maximum density in the confined region extending over  $D = 0.07 \mu\text{m}$  verifies  $F/D - Cn^3 = 0$ , i.e.,  $n = 5 \times 10^{20} \text{ cm}^{-3}$ , much lower than the value of  $4 \times 10^{22} \text{ cm}^{-3}$  quoted by the authors. (Note that this density does not vary very much with  $D$ .)

Moreover, a  $4 \times 10^{22} \text{ cm}^{-3}$  plasma can never last 70 ns. After the pulse, the time evolution of the plasma density is ruled by  $dn/dt = -n/\tau(n)$ ,

where  $\tau(n) \sim \tau_0 + 1/Cn$ . So the density decreases from  $n_i$  to  $n$  in a time  $t$  given by

$$t = \tau_0 \ln \frac{n_i}{n} + \frac{1}{2Cn_i^2} \left( \frac{n_i^2}{n^2} - 1 \right);$$

starting from  $n_i = 4 \times 10^{22} \text{ cm}^{-3}$ ,  $n = 4 \times 10^{20} \text{ cm}^{-3}$  at  $t = 35 \text{ ps}$  and  $n = 5 \times 10^{18} \text{ cm}^{-3}$  70 nsec after the pulse! As we believe that electron-phonon interaction and Auger recombination exist, we<sup>4</sup> cannot understand an  $e-h$  plasma density of  $4 \times 10^{22} \text{ cm}^{-3}$  lasting 70 ns.

(3) Finally, the crystalline phase of covalent Si is no longer the thermodynamically stable phase of Si when the density of  $e-h$  is greater than  $8 \times 10^{21} \text{ cm}^{-3}$  at 0 K. Heine and Van Vechten<sup>5</sup> have shown that at such a density the transverse-acoustic modes go to zero frequency and the crystal becomes liquid at 0 K. For higher temperature one of us (J.B.)<sup>6</sup> has estimated the critical density  $n_p$  for the melting of silicon. At 600 K,  $n_p = 3 \times 10^{21} \text{ cm}^{-3}$ . So at  $4 \times 10^{22} \text{ cm}^{-3}$ , the stable phase is the liquid one.

In summary, we think that the experimental optical properties reported by the authors are not due to a dense  $e-h$  plasma for three main reasons. The absorption of a plasma with a density of  $4 \times 10^{22} \text{ cm}^{-3}$  is that of a metal with a Fermi energy of 10 eV; such a high-density plasma cannot exist during 70 ns because of Auger recombination; and at densities higher than  $8 \times 10^{21} \text{ cm}^{-3}$ , the thermodynamically stable phase is the liquid one.

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<sup>2</sup>J. A. Van Vechten and M. Wautelet, Phys. Rev. B **23**, 5543 (1981).

<sup>3</sup>See, for example, M. Combescot and P. Nozières, J. Phys. C **5**, 2369 (1972).

<sup>4</sup>M. Combescot, Phys. Lett. **85A**, 308 (1981).

<sup>5</sup>V. Heine and J. A. Van Vechten, Phys. Rev. B **13**, 1622 (1976).

<sup>6</sup>J. Bok, Phys. Lett. **84A**, 448 (1981).